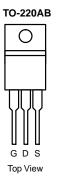
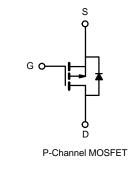


P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω) Max.	I _D (A)	Q _g (Typ.)	
- 60	0.0600 at V _{GS} = - 10 V	- 30	67	
	0.0850 at V_{GS} = - 4.5 V	- 24	07	





FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Power Switch
- · Load Switch in High Current Applications
- DC/DC Converters

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 60	- V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current ($T_1 = 150 \text{ °C}$)	T _C = 25 °C		- 30		
$Continuous Drain Current (1) = 150^{\circ} C)$	T _C = 70 °C	'D	- 29	A	
Pulsed Drain Current (t = 300 µs)		I _{DM}	- 100		
Avalanche Current		I _{AS}	- 32		
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	51	mJ	
	T _C = 25 °C	Р	41.7 ^b	10/	
Maximum Power Dissipation ^a	T _A = 25 °C ^c	P _D	2.1	- W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	60	°C 44/	
Junction-to-Case (Drain)	R _{thJC}	3	°C/W	

Notes:

a. Duty cycle \leq 1 %.

b. See SOA curve for voltage derating.

c. When mounted on 1" square PCB (FR-4 material).

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 V, I_{D} = -250 \mu A$	- 60			v
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 1		- 2.5	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 250	nA
Zero Gate Voltage Drain Current		$V_{DS} = -60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			- 1	μΑ
	I _{DSS}	$V_{DS} = -60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 \text{ °C}$			- 50	
		$V_{DS} = -60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 150 ^{\circ}\text{C}$			- 250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le$ - 10 V, V_{GS} = - 10 V	- 30			А
Drain-Source On-State Resistance ^a	D	V _{GS} = - 10 V, I _D = - 14 A		0.055	0.060	Ω
	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 12 A		0.075	0.085	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 20 V, I _D = - 14 A		40		S
Dynamic ^b	•	·		•		
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = - 20 V, f = 1 MHz		2765		pF
Output Capacitance	C _{oss}			330		
Reverse Transfer Capacitance	C _{rss}			280		
Total Gate Charge ^c	Qg			67	100	nC
Gate-Source Charge ^c	Q _{gs}	V _{DS} = - 20 V, V _{GS} = - 10 V, I _D = - 14 A		13.5		
Gate-Drain Charge ^c	Q _{gd}			14		
Gate Resistance	Rg	f = 1 MHz	0.5	2.5	5	Ω
Turn-On Delay Time ^c	t _{d(on)}			10	20	
Rise Time ^c	t _r	$V_{DD} = -20 \text{ V}, \text{ R}_{L} = 2 \Omega$ $\text{I}_{D} \cong -10 \text{ A}, \text{ V}_{\text{GEN}} = -10 \text{ V}, \text{ R}_{g} = 1 \Omega$		11	20	- ns
Turn-Off Delay Time ^c	t _{d(off)}			42	63	
Fall Time ^c	t _f			12	20	
Drain-Source Body Diode Ratings a	nd Characteri	stics T _C = 25 °C ^b				
Continuous Current	۱ _S				- 36	- A
Pulsed Current	I _{SM}				- 100	
Forward Voltage ^a	V _{SD}	I _F = - 10 A, V _{GS} = 0 V		- 0.8	- 1.5	V
Reverse Recovery Time	t _{rr}			38	57	ns
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = - 10 A, dl/dt = 100 A/μs		2.3	3.5	А
Reverse Recovery Charge	Q _{rr}	1 · · · · · · · · · · · · · · · · · · ·		40	60	nC

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

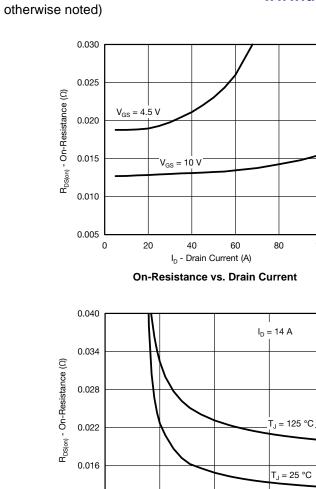


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100

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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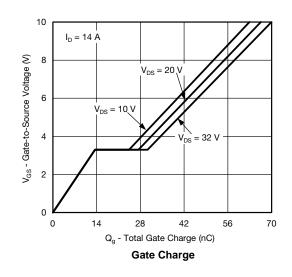
0.010 L

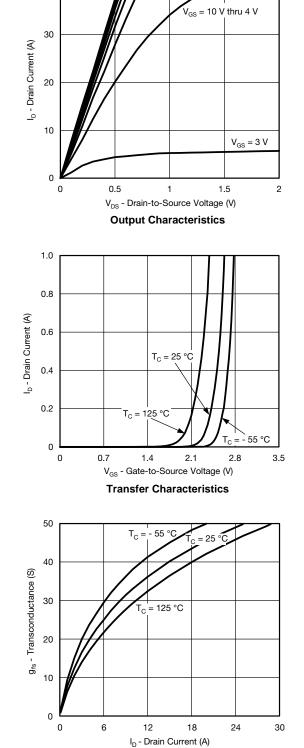


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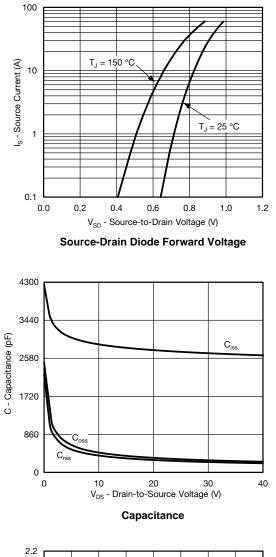
10

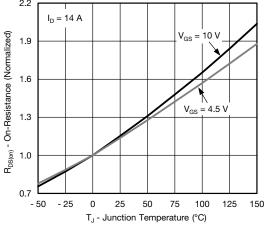




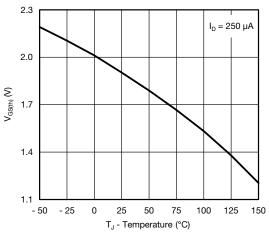
Transconductance

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

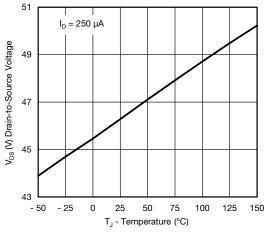




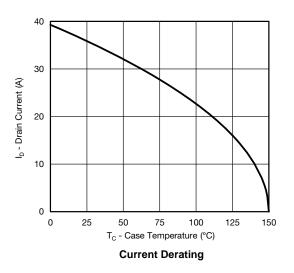
On-Resistance vs. Junction Temperature



Threshold Voltage

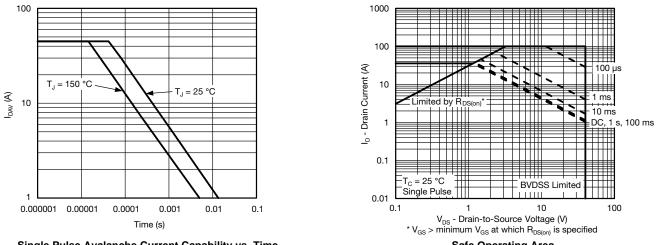


Drain Source Breakdown vs. Junction Temperature



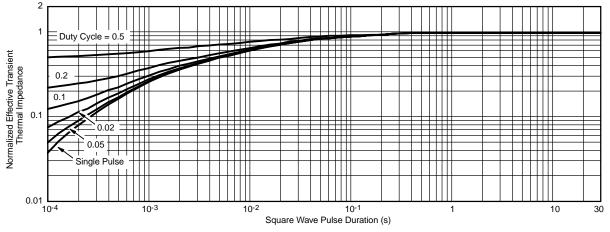


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case



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